

FUJI POWER MOSFET

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

($T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V_{DS}	900	V
	V_{DSX}^*5	900	V
Continuous drain current	I_D	± 9	A
Pulsed drain current	$I_{D(puls)}$	± 36	A
Gate-source voltage	V_{GS}	± 30	V
Repetitive or non-repetitive	I_{AR}^*2	9	A
Maximum Avalanche Energy	E_{AS}^*1	287.7	mJ
Maximum Drain-Source dV/dt	dV_{DS}/dt^*4	40	kV/ μs
Peak Diode Recovery dV/dt	dV/dt^*3	5	kV/ μs
Max. power dissipation	P_D $T_a=25^\circ\text{C}$	2.02	W
	$T_c=25^\circ\text{C}$	270	
Operating and storage temperature range	T_{ch}	+150	$^\circ\text{C}$
	T_{stg}	-55 to +150	$^\circ\text{C}$

*1 $L=6.51\text{mH}$, $V_{CC}=90\text{V}$, $T_{ch}=25^\circ\text{C}$ See to Avalanche Energy Graph *2 $T_{ch} \leq 150^\circ\text{C}$

*3 $I_F \leq -I_D$, $-di/dt=50\text{A}/\mu\text{s}$, $V_{CC} \leq B_{V_{DS}}$, $T_{ch} \leq 150^\circ\text{C}$ *4 $V_{DS} \leq 900\text{V}$ *5 $V_{GS} = -30\text{V}$

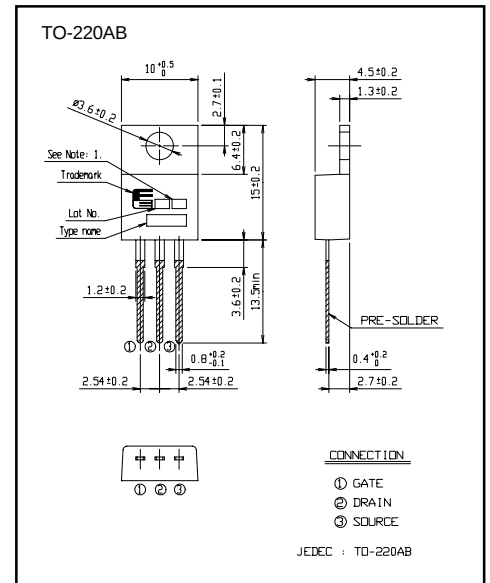
Electrical characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$ $V_{GS}=0\text{V}$	900			V
Gate threshold voltage	$V_{GS(th)}$	$I_D = 250\mu\text{A}$ $V_{DS}=V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=900\text{V}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$			25	μA
		$V_{DS}=720\text{V}$ $V_{GS}=0\text{V}$ $T_{ch}=125^\circ\text{C}$			250	
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$			100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=4.5\text{A}$ $V_{GS}=10\text{V}$		1.22	1.58	Ω
Forward transconductance	g_{fs}	$I_D=4.5\text{A}$ $V_{DS}=25\text{V}$	5	10		S
Input capacitance	C_{iss}	$V_{DS}=25\text{V}$		1100	1650	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$		140	210	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$		8	12	
Turn-on time t_{on}	$t_{d(on)}$	$V_{CC}=600\text{V}$ $I_D=4.5\text{A}$		25	38	ns
	t_r	$V_{GS}=10\text{V}$		12	18	
Turn-off time t_{off}	$t_{d(off)}$	$R_{GS}=10\Omega$		50	75	
	t_f			12	18	
Total Gate Charge	Q_G	$V_{CC}=450\text{V}$		31	46.5	nC
Gate-Source Charge	Q_{GS}	$I_D=9\text{A}$		4.5	8	
Gate-Drain Charge	Q_{GD}	$V_{GS}=10\text{V}$		11	16.5	
Avalanche capability	I_{AV}	$L=6.51\text{mH}$ $T_{ch}=25^\circ\text{C}$	9			A
Diode forward on-voltage	V_{SD}	$I_F=9\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		0.90	1.50	V
Reverse recovery time	t_{rr}	$I_F=9\text{A}$ $V_{GS}=0\text{V}$		3.2		μs
Reverse recovery charge	Q_{rr}	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		15.5		μC

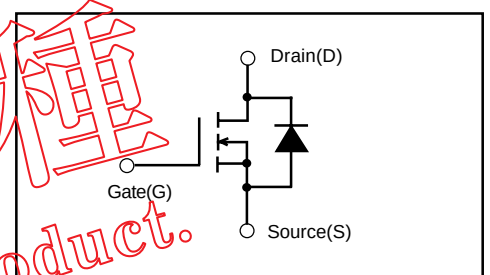
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			0.463	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			62.0	$^\circ\text{C}/\text{W}$

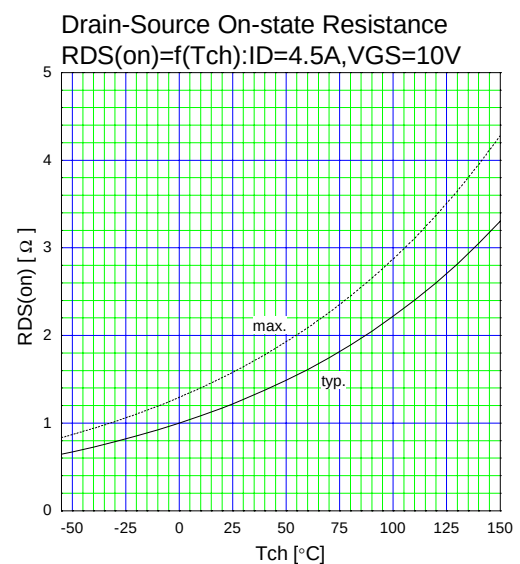
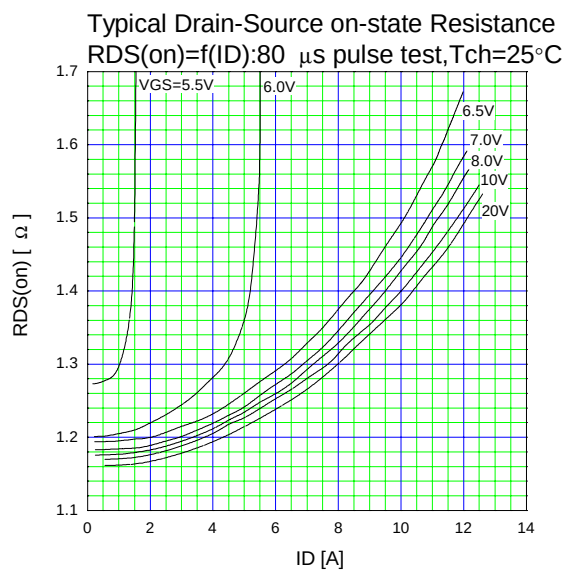
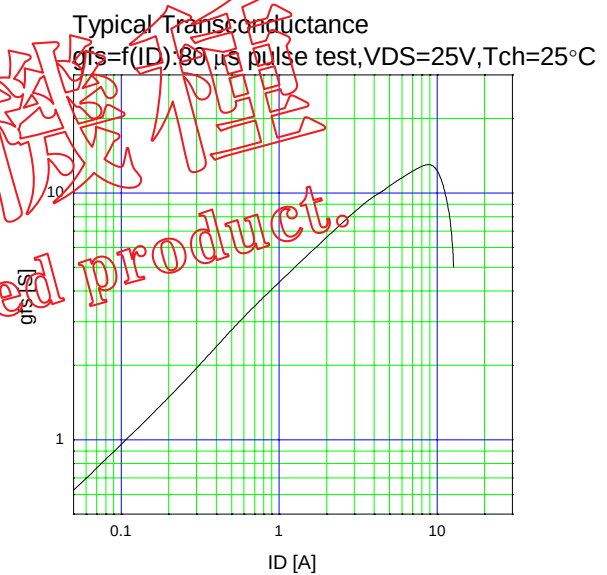
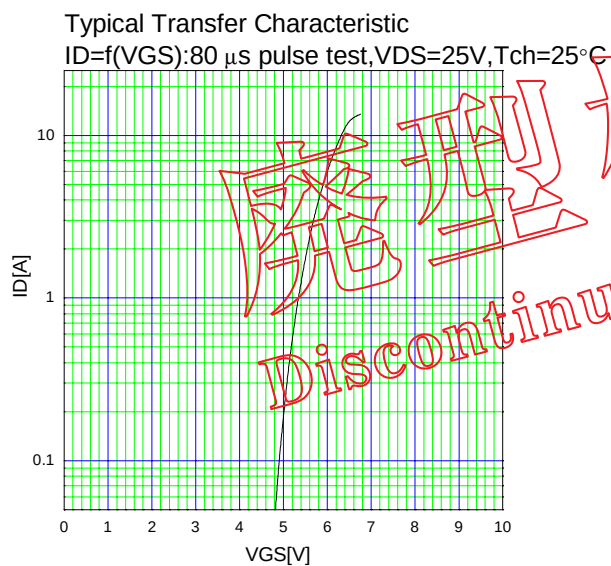
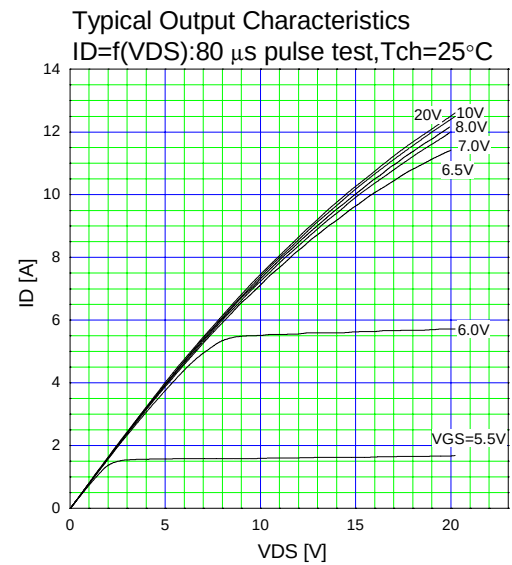
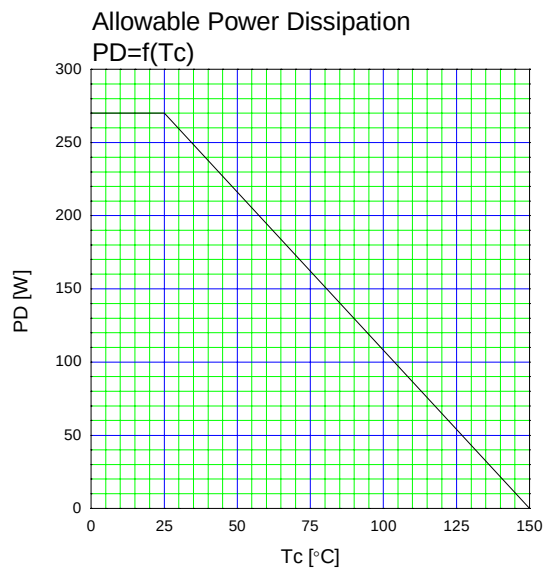
Outline Drawings [mm]

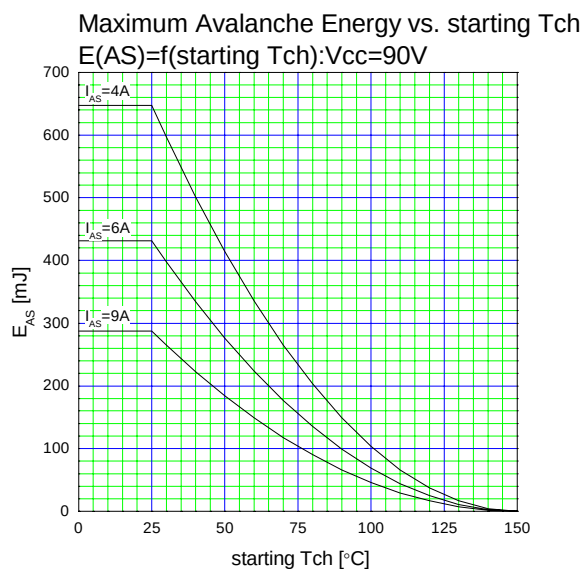
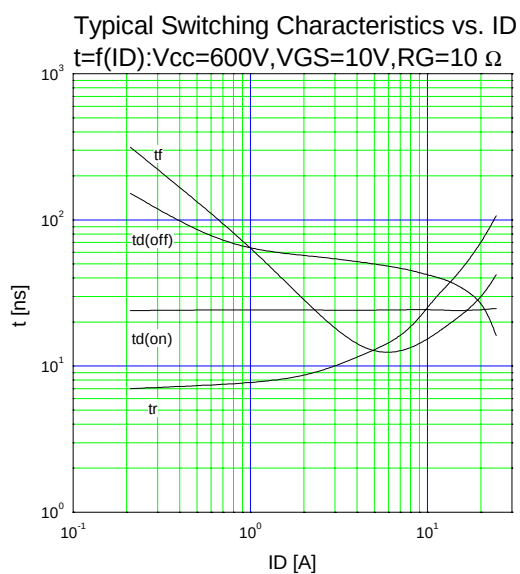
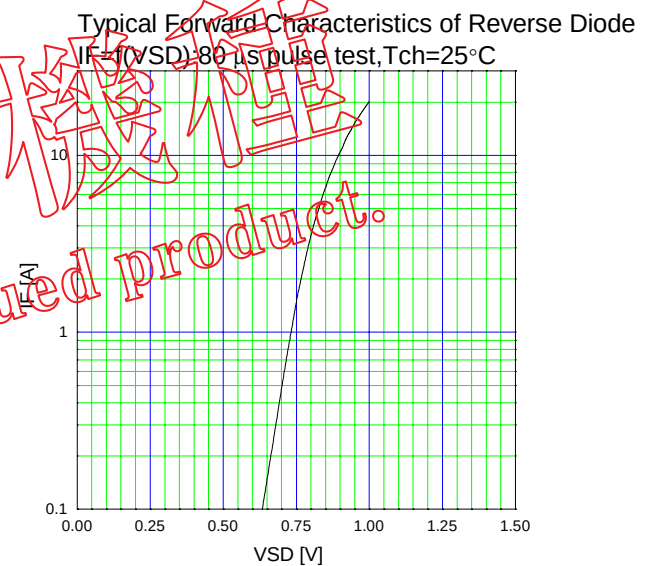
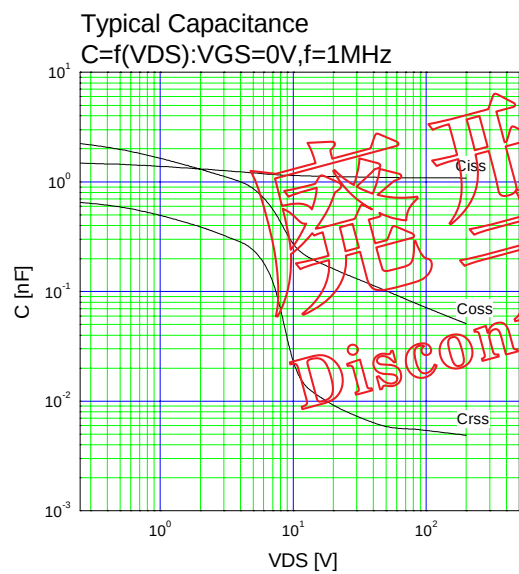
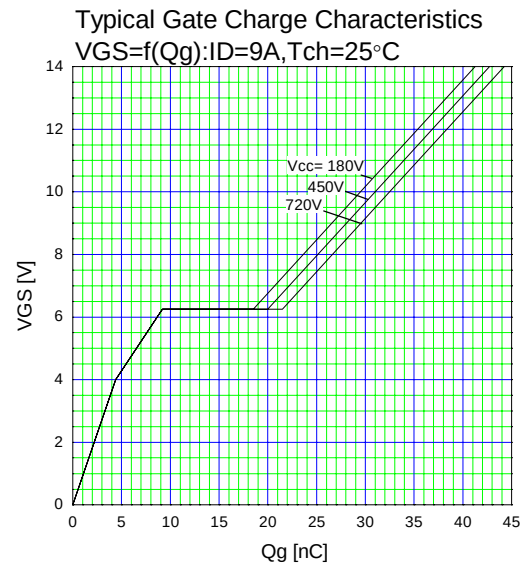
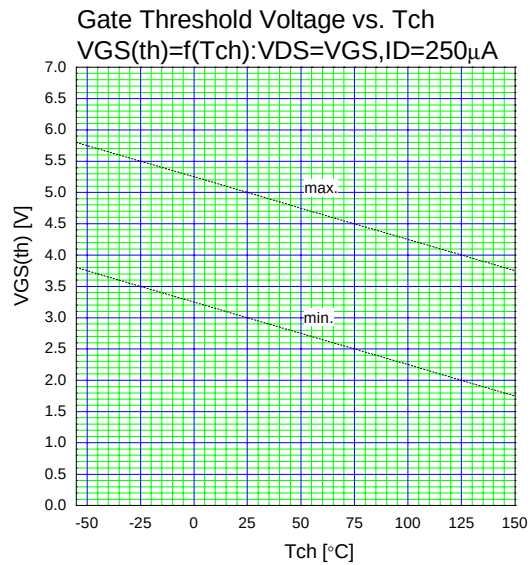


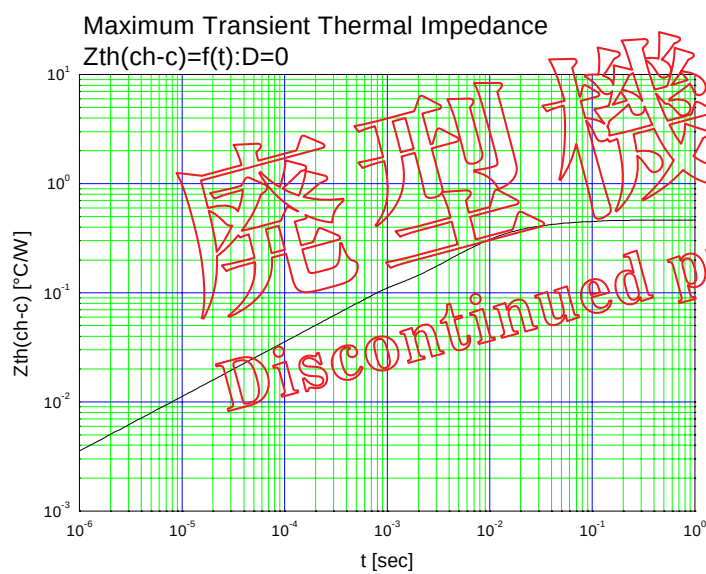
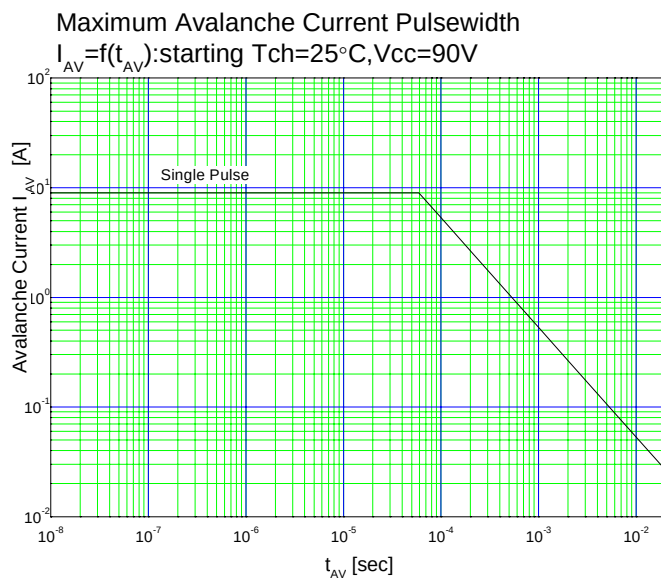
Equivalent circuit schematic



Characteristics







廢型機種
Discontinued product.